

1200 W motor control power board based on STGIB10CH60TS-L SLLIMM™ 2nd series IPM

Introduction

The STEVAL-IPM10B is a compact motor drive power board based on SLLIMM™ (small low-loss intelligent molded module) 2nd series (STGIB10CH60TS-L). It provides an affordable and easy-to-use solution for driving high power motors for a wide range of applications such as power white goods, air conditioning, compressors, power fans, high-end power tools and 3-phase inverters for motor drives in general. The IPM itself consists of short-circuit rugged IGBTs and a wide range of features like undervoltage lockout, smart shutdown, embedded temperature sensor and NTC, and overcurrent protection.

The main characteristics of this evaluation board are small size, minimal BOM and high efficiency. It consists of an interface circuit (BUS and V_{CC} connectors), bootstrap capacitors, snubber capacitor, hardware short-circuit protection, fault event and temperature monitoring. In order to increase the flexibility, it is designed to work in single- or three-shunt configuration and with double current sensing options such as using three dedicated onboard op-amps, or op-amps embedded in the MCU. The Hall/ Encoder part completes the circuit.

Thanks to these advanced characteristics, the system has been specifically designed to achieve fast and accurate current feedback conditioning, satisfying the typical requirements for field-oriented control (FOC).

The STEVAL-IPM10B is compatible with ST's STM32-based control board, enabling designers to build a complete platform for motor control.

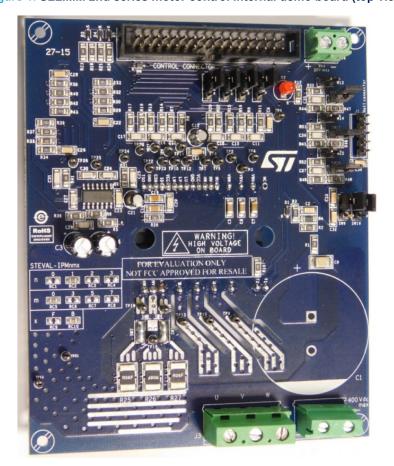


Figure 1. SLLIMM 2nd series motor control internal demo board (top view)

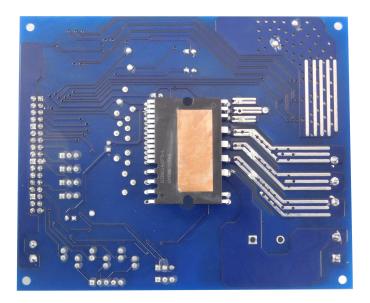


1 Key features

Input voltage: 125 - 400 VDC
Nominal power: up to 700 W
Nominal current: up to 7 A

- Input auxiliary voltage: up to 20 V DC
- Motor control connector (32 pins) interfacing with ST MCU boards
- Single- or three-shunt resistors for current sensing (with sensing network)
- Two options for current sensing: dedicated op-amps or through MCU
- Overcurrent hardware protection
- IPM temperature monitoring and protection
- Hall sensors (3.3 / 5 V)/encoder inputs (3.3 / 5 V)
- IGBT intelligent power module:
 - SLLIMM™ 2nd series IPM (STGIB10CH60TS-L Full molded package)
- · Universal conception for further evaluation with bread board and testing pins
- Very compact size

Figure 2. SLLIMM 2nd series motor control internal demo board: (bottom view)



UM2018 - Rev 3 page 2/35



2 Circuit schematics

Following figures show the whole schematic of the SLLIMM $^{\text{TM}}$ 2nd series card for STGIB10CH60TS-L IPM products. This card consists of an interface circuit (BUS and V_{CC} connectors), bootstrap capacitors, snubber capacitor, short-circuit protection, fault output circuit, temperature monitoring, single-/three-shunt resistors and filters for input signals. It also includes bypass capacitors for V_{CC} and bootstrap capacitors. The capacitors are located very close to the drive IC, which is very helpful in preventing malfunction due to noise.

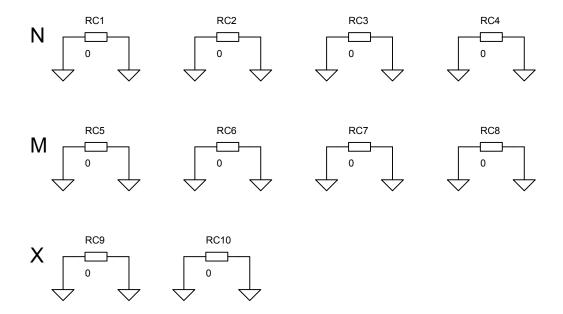
Two current sensing options are provided: three dedicated onboard op-amps or using opamps embedded on the MCU. Selection is performed through three jumpers.

The Hall/Encoder part (powered at 5 V or 3.3 V) completes the circuit.

2.1 Schematic diagram

Figure 3. STEVAL-IPM10B circuit schematic (1 of 6)

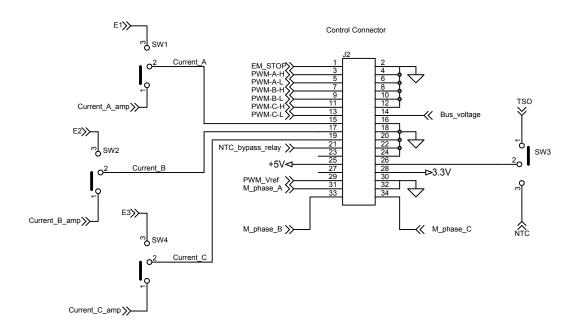
STEVAL-IPMnmx decoder

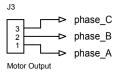


UM2018 - Rev 3 page 3/35



Figure 4. STEVAL-IPM10B circuit schematic (2 of 6)

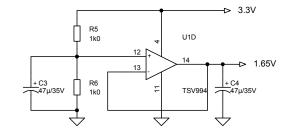




UM2018 - Rev 3 page 4/35



Figure 5. STEVAL-IPM10B circuit schematic (3 of 6)



UM2018 - Rev 3 page 5/35



R36 TSV994 U1C R39 R34 2K1 100 Z 140 R35 1k0 1.65∨ 4 R37 3300 238 3.3 R31 R41 * C23 3.30 TSV994 TSV994 U1B 15 H U1A 4.7u 50V R29 2K1 R33 2K1 R38 2K1 R43 2K1 R40 1k0 C30 100 140 100p R30 1k0 . 8 R42 R32 1.65∨ 4

Figure 6. STEVAL-IPM10B circuit schematic (4 of 6)

UM2018 - Rev 3 page 6/35



E3 E2 П R27 0.06 C9 0,1 uF - 400V Swe \Diamond R26 0.06 SW5 HP1 R10 12k ₽D-를 D→ 를 D ₹ D R25 0.06 R24 1k0 R18 1k0 R21 1k0 IPM module STGIB10CH60TS-L VCCH 1k0 - 5 t - 6 t - 6 t 4 E Y C5 22u ₽<u></u> ,≅D R53 4.7k ₽D -□ 월 3.3V -19d 10p 유 문 무 음후 ₹ 2 0 5 g R28 10k R9 1k0 R20 1k0 R14 1k0 £88. R 243 R22 3K3 PWM-A-L ≫ PWM-A-H ≫ PWM-B-L PWM-C-L ≫ D2 LED Red Phase A - input Phase C - input Phase B - input ₩ 1752 1753 17

Figure 7. STEVAL-IPM10B circuit schematic (5 of 6)

UM2018 - Rev 3 page 7/35



M_phase_C M_phase_A M_phase_B SW15 R52 4k7 SW14 R51 4k7 SW13 R50 4k7 R46 j 4k7 C37 R45 4K7 C36 10p R44 4K7 C35 Hall/Encoder 2k4 2k4 2k4 SW12 SW11 R47 **R**48 R49 100n က<mark>ြ</mark> SW16 Encoder/Hall H1/A+ H2/B+ H3/Z+ + 3.3/5V GND

Figure 8. STEVAL-IPM10B circuit schematic (6 of 6)

3.3V

UM2018 - Rev 3 page 8/35



3 Main characteristics

The board is designed to be compatible with DC supply from 125 VDC up to 400 VDC voltage.

A bulk capacitor according to the power level of the application must be mounted. The footprint is already provided on the board.

The SLLIMM integrates six IGBT switches with freewheeling diodes together with high voltage gate drivers. Thanks to this integrated module, the system is specifically designed to achieve power inversion in a reliable and compact design. Such integration reduces the required PCB area and the simplicity of the design increases reliability.

In order to increase the flexibility, it can operate in single- or three-shunt configuration by modifying solder bridge jumper settings (see Section 4.3.5 Single- or three-shunt selection).

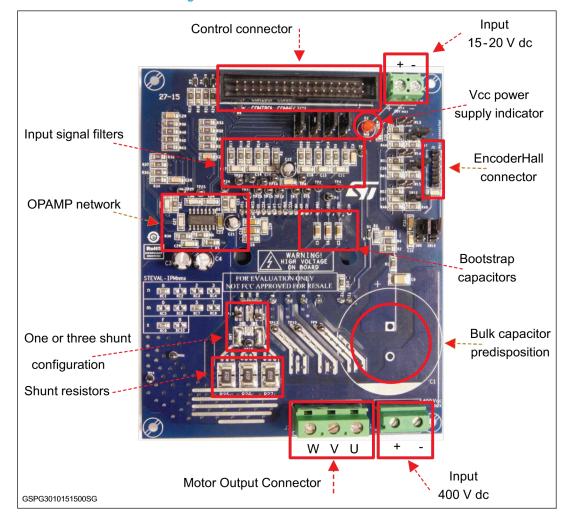


Figure 9. STEVAL-IPM05F architecture

UM2018 - Rev 3 page 9/35



4 Filters and key parameters

4.1 Input signals

The input signals (LINx and HINx), able to drive the internal IGBTs, are active high. A 100 k Ω (typ.) pull-down resistor is built-in for each input signal. In order to prevent input signal oscillation, an RC filter was added on each input and placed as close as possible to the IPM. The filter is designed using a time constant of 10 ns (1 k Ω and 10 pF).

4.2 Bootstrap capacitor

In the 3-phase inverter, the emitters of the low side IGBTs are connected to the negative DC bus (V_{DC-}) as common reference ground, which allows all low side gate drivers to share the same power supply, while the emitter of high side IGBTs is alternately connected to the positive (V_{DC+}) and negative (V_{DC-}) DC bus during running conditions.

A bootstrap method is a simple and cheap solution to supply the high voltage section. This function is normally accomplished by a high voltage fast recovery diode. The SLLIMM 2^{nd} series family includes a patented integrated structure that replaces the external diode. It is realized with a high voltage DMOS functioning as diode with series resistor. An internal charge pump provides the DMOS driving voltage. The value of the C_{BOOT} capacitor should be calculated according to the application condition.

Figure 10. C_{BOOT} graph selection shows the behavior of C_{BOOT} (calculated) versus switching frequency (f_{sw}), with different values of ΔV_{CBOOT} for a continuous sinusoidal modulation and a duty cycle δ = 50%.

The boot capacitor must be two or three times larger than the C_{BOOT} calculated in the graph. For this design, a value of 2.2 μ F was selected.

Note:

This curve is taken from application note AN4768 (available on www.st.com); calculations are based on the STGIB15CH60 device, which represents the worst case scenario for this kind of calculation.

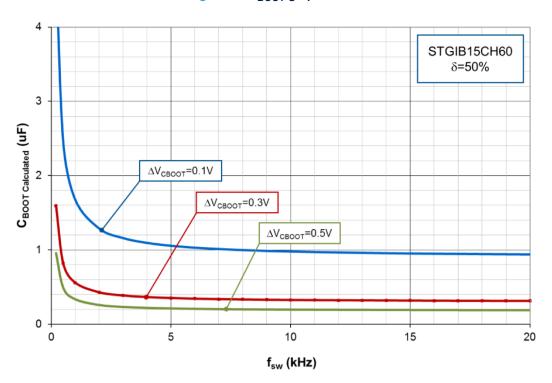


Figure 10. C_{BOOT} graph selection

UM2018 - Rev 3 page 10/35



4.3 Overcurrent protection

The SLLIMM 2^{nd} series integrates a comparator for fault sensing purposes. The comparator has an internal voltage reference V_{REF} (510 mV typ.) connected to the inverting input, while the non-inverting input available on the CIN pin can be connected to an external shunt resistor to implement the overcurrent protection function. When the comparator triggers, the device enters the shutdown state.

The comparator output is connected to the SD pin in order to send the fault message to the MCU.

4.3.1 SD Pin

The \overline{SD} is an input/output pin (open drain type if used as output). Taking into account the voltage reference on \overline{SD} (3.3 V), a pull up resistor of 10 k Ω (R28) is used to guarantee the right bias and consequently to keep the current on the open drain DMOS (I_{od}) lower than 3 mA.

The filter on \overline{SD} (R28 and C20) has to be sized to obtain the desired re-starting time after a fault event and placed as close as possible to the \overline{SD} pin.

A shutdown event can be managed by the MCU, in this case the \overline{SD} functions as the input pin.

Conversely, the \overline{SD} functions as an output pin when an overcurrent or undervoltage condition is detected.

4.3.2 Fault management

The SLLIMM 2nd series integrates a specific kind of fault management, useful when SD is functioning as output, able to identify the type of fault event.

As previously described, as soon as a fault occurs, the open-drain (DMOS) is activated and LVGx outputs are forced low.

Two types of fault can be signaled:

- Overcurrent (OC) sensed by the internal comparator (CIN);
- Undervoltage (UVLO) on supply voltage (VCC).

Each fault enables the SD open drain for a different time (see the table below).

The duration of a shutdown event therefore tells us the type of failure that has occurred.

Symbol Parameter Event time SD open-drain enable time result ≤ 24 µs 24 µs OC Over current event > 24 µs OC time ≤ 70 µs 70 µs > 70 µs until VCC LS **UVLO** Undervoltage lockout event **UVLO** time exceeds the VCC LS UV turn on threshold

Table 1. Fault timing

2. without contribution of RC network on SD

Figure 11. SD failure due to overcurrent shows a shutdown as the result of an overcurrent event. During the overcurrent, the voltage on the comparator (CIN) exceeds the threshold (0.51 V typ.) and the shutdown is able to stop the application. In this case, the SD event time is about 24 µs (for OC event less than 24 µs).

UM2018 - Rev 3 page 11/35

^{1.} typical value ($T_J = -40 \, ^{\circ}\text{C}$ to 125 $^{\circ}\text{C}$)



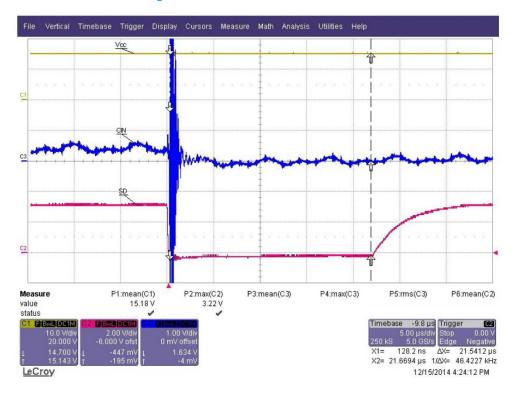


Figure 11. SD failure due to overcurrent

Figure 12. SD failure due to undervoltage (UVLO below 70 μ s) shows the shutdown event as the result of an undervoltage condition on the V_{CC} supply. If V_{CC} drops below the undervoltage threshold, the shutdown can stop the application. If the voltage on V_{CC} rises above the V_{CC} on threshold in less than 70 μ s, the SD event time is about 70 μ s.

UM2018 - Rev 3 page 12/35



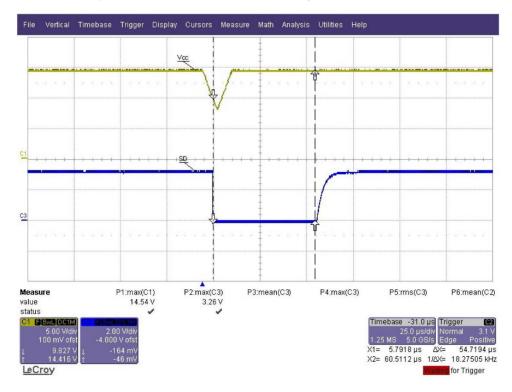


Figure 12. SD failure due to undervoltage (UVLO below 70 μs)

Figure 13. SD failure due to undervoltage (UVLO above 70 μ s) shows the shutdown event as the result of an undervoltage condition on the V_{CC} supply. In this case, the drop on V_{CC} is greater than 70 μ s. The SD event time is the same as the duration of drop.

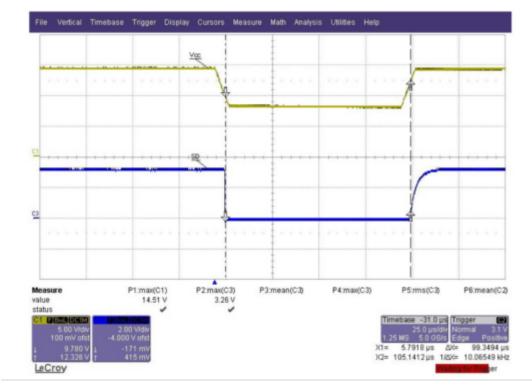


Figure 13. SD failure due to undervoltage (UVLO above 70 µs)

UM2018 - Rev 3 page 13/35



4.3.3 Shunt resistor selection

The value of the shunt resistor is calculated by the following equation:

$$R_{SH} = \frac{V_{ref}}{I_{OC}} \tag{1}$$

Where V_{ref} is the internal comparator (CIN) (0.51 V typ.) and I_{OC} is the overcurrent threshold detection level.

The maximum OC protection level should be set to less than the pulsed collector current in the datasheet. In this design, the overcurrent threshold level is fixed at I_{OC} = 13 A in order to select a commercial shunt resistor value.

$$R_{SH} = \frac{V_{ref} \cdot \left(\frac{R23 + R53}{R53}\right) + V_F}{I_{OC}} = \frac{0.51 \cdot \left(\frac{1000 + 4700}{4700}\right) + 0.18}{13} = 0.061\Omega$$
 (2)

Where V_F is the voltage drop across diodes D6, D7 and D8.

For the power rating of the shunt resistor, the following parameters must be considered:

- Maximum load current of inverter (85% of I_{nom [Arms]}): I_{load(max)}
- Shunt resistor value at TC = 25 °C
- Power derating ratio of shunt resistor at T_{SH} =100 °C
- · Safety margin

The power rating is calculated by the following equation:

$$P_{SH} = \frac{1}{2} \cdot \frac{I_{load(max)}^{2} \cdot R_{SH} \cdot margin}{Derating\ gratio}$$
 (3)

The commercial value chosen was $0.06~\Omega$ to which corresponds an overcurrent level of 13.3 A.

The power rating is:

•
$$I_{nom} = 7A \rightarrow I_{nom[rms]} = \frac{I_{nom}}{\sqrt{2}} \rightarrow I_{load(max)} = 85\%$$

$$\left(I_{nom[rms]}\right) = 6 A_{rms}$$
(4)

- Power derating ratio of shunt resistor at TSH = 100 °C: 80% (from datasheetmanufacturer)
- Safety margin: 30%

$$P_{SH} = \frac{1}{2} \cdot \frac{6.0^2 \cdot 0.06 \cdot 1.3}{0.8} = 1.75 \, W \tag{5}$$

Considering the commercial value, a 1 W shunt resistor was selected.

Based on the previous equations and conditions, the minimum shunt resistance and power rating is summarized below.

Table 2. Shunt selection

Device	I _{nom(peak)} [A]	OCP _(peak) [A]	I _{load(max)} [Arms]	R _{SHUNT} [Ω]	Minimum shunt power rating P _{SH} [W]
STGIB10CH60TS-L	10	13.3	6.0	0.06	1.75

4.3.4 RC filter

An RC filter network is required to prevent undesired short circuit operation due to the noise on the shunt resistor. In this design, the RC filter, composed of R23, R18, R21, R24 and C19, has a constant time of about 1.3 μ s. Adding the turn-off propagation delay of the gate driver and the IGBT turn-off time (hundreds of nanoseconds in total), the total delay time is less than 5 μ s of short circuit withstand IGBT time.

4.3.5 Single- or three-shunt selection

Single- or three-shunt resistor circuits can be adopted by setting the solder bridges SW5, SW6, SW7 and SW8. The figures below illustrate how to set up the two configurations.

UM2018 - Rev 3 page 14/35



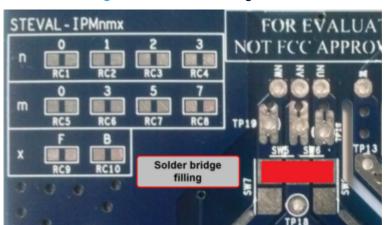
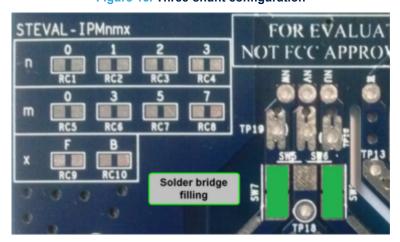


Figure 14. One-shunt configuration





UM2018 - Rev 3 page 15/35



5 Current sensing amplifying network

The motor control demonstration board can be configured to run in three-shunt or single-shunt configurations for field oriented control (FOC).

The current can be sensed thanks to the shunt resistor and amplified by using the on board operational amplifiers or by the MCU (if equipped with op-amp).

Once the shunt configuration is chosen by setting solder bridge on SW5, SW6, SW7 and SW8 (as described in Section 4.3.5 Single- or three-shunt selection), the user can choose to send the voltage shunt to the MCU amplified or unamplified.

Single-shunt configuration requires a single op amp and three-shunt configuration requires three op amps; therefore, in single-shunt configuration, the only voltage which is sent to the MCU to control the sensing is connected to phase V through SW2.

SW1, SW2, SW4 can select which signals are sent to micro, as described below:

Symbol	Configuration	Bridge	Sensing
	Single	1-2	open
SW1	Shunt	2-3	open
SWI	Three	1-2	On-board op-amp
	Shunt	2-3	MCU op-amp
	Single	1-2	On board op-amp
SW2	Shunt	2-3	MCU op-amp
3002	Three	1-2	On-board op-amp
	Shunt	2-3	MCU op-amp
	Single	1-2	open
SW4	Shunt	2-3	open
3004	Three	1-2	On-board op-amp
	Shunt	2-3	MCU op-amp

Table 3. Op-amp sensing configuration

The operational amplifier TSV994 used on amplifying networks has a 20 MHz gain bandwidth and operates with a single positive supply of 3.3 V.

The amplification network must allow bidirectional current sensing, so that an output offset $V_O = +1.65 \text{ V}$ represents zero current.

Referencing the STGIB10CH60TS-L (I_{OCP} = 13.3 A; R_{SHUNT} = 0.06 Ω), the maximum measurable phase current, considering that the output swings from +1.65 V to +3.3 V (MCU supply voltage) for positive currents and from +1.65 V to 0 for negative currents is:

Equation 5

$$MaxMeasCurrent = \frac{\Delta V}{r_m} = 13.3 A \tag{6}$$

$$r_{m} = \frac{\Delta V}{MaxMeasCurrent} = \frac{1.65}{13.3} = 0.124 \,\Omega \tag{7}$$

The overall trans-resistance of the two-port network is:

$$r_m = R_{SHUNT} \cdot AMP = 0.06 \cdot AMP = 0.124 \Omega \tag{8}$$

$$AMP = \frac{r_m}{R_{SHUNT}} = \frac{0.124}{0.06} = 2.1 \tag{9}$$

Finally choosing R_a=R_b and R_c=R_d, the differential gain of the circuit is:

UM2018 - Rev 3 page 16/35



$$AMP = \frac{R_C}{R_a} = 2.1 \tag{10}$$

An amplification gain of 2.1 was chosen. The same amplification is obtained for all the other devices, taking into account the OCP current and the shunt resistance, as described in Table 1.

The RC filter for output amplification is designed to have a time constant that matches noise parameters in the range of 1.5 μ s:

$$4 \cdot \tau = 4 \cdot R_e \cdot C_c = 1.5 \,\mu s \tag{11}$$

$$C_C = \frac{1.5 \,\mu s}{4 \cdot 1000} = 375 \,pF \left(330 \,pF \,selected\right)$$
 (12)

Table 4. Amplifying networks

Phase		Amplifying network			RC t	filter
Phase	Ra	Rb	Rc	Rd	Re	Сс
Phase U	R30	R32	R29	R33	R31	C25
Phase V	R35	R37	R34	R39	R36	C29
Phase W	R40	R42	R38	R43	R41	C31

UM2018 - Rev 3 page 17/35



6 Temperature monitoring

The SLLIMM 2nd series family integrates a temperature sensor (VTSO) on the low side gate driver and an NTC thermistor placed close to the power stage.

They can be selected via SW3.

The board is designed to use both of them to monitor the internal IPM temperature through the MCU.

6.1 Thermal sensor (VTSO)

A voltage proportional to the temperature is available on the TSO pin (17) and easily measurable on the TP20 test pin.

To improve noise immunity, a 1 nF (C16) capacitor filter is placed on this pin.

The thermal sensor does not need any pull down resistors.

The following graph shows typical voltage variation as a function of temperature.

3.5 3.0 2.5 2.0 OS 1.5 1.0 0.5 0.0 25 50 75 100 125

Figure 16. Thermal sensor voltage vs temperature

6.2 NTC Thermistor

The embedded thermistor (85 kΩ at 25 °C) in the IPM is connected between pins T1 and T2 (26, 25).

A12 $k\Omega$ pull up resistor (R10) ensures that the voltage variation on the NTC as a function of temperature is almost linear. This voltage is easily monitored on TP1 test pin.

T[°C]

The figure below shows the typical voltage on T2 as function of temperature.

UM2018 - Rev 3 page 18/35

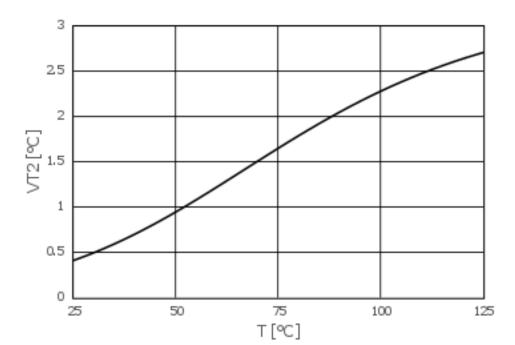


Figure 17. NTC voltage vs temperature

UM2018 - Rev 3 page 19/35



7 Firmware configuration for STM32 PMSM FOC SDK

The following table summarizes the parameters which customize the latest version of the ST FW motor control library for permanent magnet synchronous motor (PMSM): STM32 PMSM FOC SDK for this STEVAL-IPM10B.

Table 5. ST motor control workbench GUI parameters

Block	Parameter	Value
	Comparator threshold	$V_{ref} \cdot \left(\frac{R23 + R53}{R53}\right) + V_F = 0.83V$ (13)
Over current protection	Overcurrent network offset	0
	Overcurrent network gain	0.1 V/A
Bus voltage sensing	Bus voltage divider	1/125
	Min rated voltage	125 V
Rated bus voltage info	Max rated voltage	400 V
	Nominal voltage	325 V
	Current reading typology	Single- or three-shunt
Current sensing	Shunt resistor value	0.06 Ω
	Amplifying network gain	2.1
	Phase U Driver	HS and LS: Active high
Command stage	Phase V Driver	HS and LS: Active high
	Phase W Driver	HS and LS: Active high

UM2018 - Rev 3 page 20/35



8 Connectors, jumpers and test pins

Table 6. Connectors

Connector	Reference	Descriptio	n / pinout
		Motor contro	ol connector
		1 - emergency stop	2 - GND
		3 - PWM-1H	4 - GND
		5 - PWM-1L	6 - GND
		7 - PWM-2H	8 - GND
	1 2	9 - PWM-2L	10 - GND
	• •	11 - PWM-3H	12 - GND
		13 - PWM-3L	14 - HV bus voltage
12	**	15 - current phase A	16 - GND
J2		17 - current phase B	18 - GND
	::	19 - current phase C	20 - GND
		21 - NTC bypass relay	22 - GND
	33 34	23 - dissipative brake PWM	24 - GND
	33	25 - +V power	26 - heat sink temperature
		27- PFC sync.	28 - VDD_m
		29 - PWM VREF	30 - GND
		31 - measure phase A	32 - GND
		33 - measure phase B	34 - measure phase C
J3	— А — в — с	Motor connector	
J4	1 1 1 2	VCC supply (20 VDC max) positive negative	
J7	1 1 1 2	Supply connector (DC – 125V to 40 1. + (positive terminal) 2 (negative terminal)	00 V)
J9	1 1 1 1 1 1 1 1 1 1 2 3 4 5	Hall sensors / encoder input conne 1. Hall sensors input 1 / encode 2. Hall sensors input 2 / encode 3. Hall sensors input 3 / encode 4. 3.3 or 5 Vdc 5. GND	er A+ er B+

UM2018 - Rev 3 page 21/35



Table 7. Jumpers

Jumper	Description	
	TSO/NTC	
SW3	TSO: jumper on 1-2	
	NTC: jumper on 2-3	
	To choose current U to send to control board:	
SW1	Jumper on 1-2: from amplification	
	Jumper on 2-3: directly from motor output	
	To choose current V to send to control board	
SW2	Jumper on 1-2: from amplification	
	Jumper on 2-3: directly from motor output	
	To choose current W to send to control board:	
SW4	Jumper on 1-2: from amplification	
	Jumper on 2-3: directly from motor output	
SW13	To modify phase A hall sensor network	
SW14	To modify phase B hall sensor network	
SW15	To modify phase C hall sensor network	
	To choose input power for Hall/Encoder	
SW9, SW16	Jumper on 1-2: 5 V	
	Jumper on 2-3: 3.3 V	
	To choose one-shunt or three-shunt configuration.	
	(Through solder bridge)	
SW5, SW6	SW5, SW6 closed	one shunt
SW7, SW8	SW7, SW8 open	One Shant
	SW5, SW6 open	three shunt
	SW7, SW8 closed	unee shunt

Table 8. Test pins

Test Pin	Description
TP1	NTC (T2 pin)
TP2	VBOOTw
TP3	VBOOTv
TP4	VBOOTu
TP5	HinU (high side U control signal input)
TP6	HinV (high side V control signal input)
TP7	HinW (high side W control signal input)
TP8	VCCH
TP9	phase A (U pin)
TP10	phase B (V pin)
TP11	Ground
TP12	LinU (high side U control signal input)

UM2018 - Rev 3 page 22/35



Test Pin	Description
TP13	phase C (W pin)
TP14	LinV (high side V control signal input)
TP15	LinW (high side W control signal input)
TP16	Negative DC input for U phase
TP17	CIN
TP18	Negative DC input for V phase
TP19	Negative DC input for W phase
TP20	TSO (TSO pin)
TP21	Ground
TP22	Ground
TP23	SD (shutdown pin)
TP24	Current_A_amp
TP25	Current_B_amp
TP26	Current_C_amp

UM2018 - Rev 3 page 23/35



9 Bill of material

The components used to build the evaluation board are listed below. The majority of the active components used are available from STMicroelectronics.

Table 9. Bill of materials

Item	Qty	Reference	Part/Value	Description	Manufacturer	Order code
1	4	C2, C22, C26, C28	10 nF, SMD 1206	Capacitor	AVX	12065C103KAT2A
2	9	C10, C11, C14, C15, C17, C18, C35, C36, C37	10 pF, SMD 1206	Capacitor	AVX	12061A100JAT2A
3	4	C20, C25, C29, C31	330 pF, SMD 1206	Capacitor	AVX	12065A331JAT2A
4	3	C5, C6, C7	2.2 μF, SMD 1206	Capacitor	Murata	GCM31MR71E225KA57L
5	6	C8, C13, C23, C32, C33, C34	100 nF, SMD 1206	Capacitor	AVX	12065C104KAZ2A
6	2	C12, C21	4.7 μF	Electrolytic capacitor	Any	Any
7	2	C19, C16	1 nF, SMD 1206	Capacitor	Kemet	C1206C102K5RACTU
8	1	C9	0.1 μF, SMD 1812	Capacitor	Murata	GRM43DR72J104KW01L
9	3	C24, C27, C30	100 pF, SMD 1206	Capacitor	Kemet	C1206C101J1GACTU
10	2	C3, C4	47 μF	Electrolytic capacitor	Any	
11	5	D1, D3, D4, D5, D6	Diode SOD323	Schottky diode	ST	BAT48J
12	1	D2	2 mA, 3 mm	Red LED	Ledtech	L4RR3000G1EP4
13	1	J2	Connector	Connector 34- pins	RS	625-7347
14	1	J3	7 mm - 3 pole	Connector	TE Connectivity AMP Connectors	282845-3
15	1	J4	5 mm - 2 pole	Connector -	Phoenix Contact	1935161
16	1	J1	7 mm - 2 pole	Connector	On Shore Technology Inc	OSTVI024152
17	1	J5	Connector	Five pins of pin header	RS	W81136T3825RC
18	2	R1, R2	$470 \text{ k}\Omega$, , SMD 1206	Resistor	Any	
19	1	R4	7.5 kΩ, SMD 1206	Capacitor	Panasonic	ERJP08F7501
20	1	R3	120 Ω, SMD 1206	Resistor	Any	Any
21	3	R7, R13, R17	3.9 kΩ, SMD 1206	Resistor	Any	Any
22	21	R5, R6, R8, R9, R14, R15, R19, R20, R23, R30, R32, R31, R18, R21, R24, R36, R35, R41, R42, R40, R37	Resistor, SMD 1206		Any	Any
23	3	R11, R16, R22	3.3 kΩ	Resistor	Any	Any
24	1	R28	10 kΩ, SMD 1206	Resistor	Any	Any
25	1	R10	12 kΩ, SMD 1206	Resistor	Any	Any

UM2018 - Rev 3 page 24/35



Item	Qty	Reference	Part/Value	Description	Manufacturer	Order code
26	6	R29, R33, R34, R38, R39, R43	2.1 kΩ, SMD 1206	Resistor	Any	Any
27	1	R12	5.6 kΩ, SMD 1206	Resistor	Any	Any
28	3	R25, R26, R27	0.06 Ω, SMD 2512	Resistor	Vishay	WSL2512R1000FEK
29	7	R44, R45, R46, R50, R51, R52, R53	4.7 kΩ, SMD 1206	Resistor	Any	Any
30	3	R47, R48, R49	2.4 kΩ, SMD 1206	Resistor	Any	Any
31	6	SW1, SW2, SW3,S W4, SW9, SW16	Jumper 2.54	Three pins of pin header	RS	W81136T3825RC
32	6	SW10, SW11, SW12, SW13, SW14, SW15	Jumper 2.54	Two pins of pin header	RS	W81136T3825RC
33	12	-	2.54 mm, low profile, connector	-	RS	881545-2
34	2	SW7, SW8		Solder bridge	Any	Any
35	2	SW5, SW6	open	-	Any	Any
36	26	TP1, TP2, TP3, TP4, TP5, TP6, TP7, TP8, TP9, TP10, TP11, TP12, TP13, TP14, TP15, TP16, TP17, TP18, TP19, TP20, TP21, TP22, TP23, TP24, TP25, TP26	PCB terminal 1 mm	Test pin	KEYSTONE	5001
37	1	U1	20 MHz GBP	Rail-to-rail input/ output operational amplifiers, SO14	ST	TSV994
38	1	U2	8 A, 600 V	SLLIMM 2nd series IPM, 3- phase inverter, short-circuit rugged IGBTs	ST	STGIF5CH60TS-L
39	3	RC1,RC6,RC9	0 Ω, SMD 0805	Resistor	Any	Any
40	7	RC2, RC3, RC4, RC5, RC7, RC8, RC10	Not mounted	Not mounted	Any	Any
41	9	to close switch for: SW1, SW2, SW3, SW4, SW9, SW10, SW11, SW12, SW16	-	-	TE Connectivity	1-881545-1

UM2018 - Rev 3 page 25/35



10 PCB design guide

Optimization of PCB layout for high voltage, high current and high switching frequency applications is a critical point. PCB layout is a complex matter as it includes several aspects, such as length and width of track and circuit areas, but also the proper routing of the traces and the optimized reciprocal arrangement of the various system elements in the PCB area.

A good layout can help the application to properly function and achieve expected performance. On the other hand, a PCB without a careful layout can generate EMI issues, provide overvoltage spikes due to parasitic inductance along the PCB traces and produce higher power loss and even malfunction in the control and sensing stages.

In general, these conditions were applied during the design of the board:

- PCB traces designed as short as possible and the area of the circuit (power or signal) minimized to avoid the sensitivity of such structures to surrounding noise.
- Good distance between switching lines with high voltage transitions and the signal line sensitive to electrical noise.
- The shunt resistors were placed as close as possible to the low side pins of the SLLIMM. To decrease the parasitic inductance, a low inductance type resistor (SMD) was used.
- RC filters were placed as close as possible to the SLLIMM pins in order to increase their efficiency.

10.1 Layout of reference board

All the components are inserted on the top of the board. Only the IPM module is inserted on the bottom to allow the insertion of a suitable heatsink for the application.

100.3

Figure 18. Silk screen and etch - top side

UM2018 - Rev 3 page 26/35



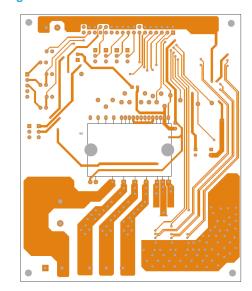


Figure 19. Silk screen and etch - bottom side

UM2018 - Rev 3 page 27/35



11 Recommendations and suggestions

- The BOM list is not provided with a bulk capacitor already inserted in the PCB. However, the necessary space has been included (C1). In order to obtain a stable bus supply voltage, it is advisable to use an adequate bulk capacity. For general motor control applications, an electrolytic capacitor of at least 100 μF is suggested.
- Similarly, the PCB does not come with a heat sink. In case of need, place an heat sink on top of the PCB with thermal conductive foil and screws. R_{TH} is an important factor for good thermal performance and depends on certain factors such as current phase, switching frequency, power factor and ambient temperature.
- The board requires +5 V and +3.3 V to be supplied externally through the 34-pin motor control connector J2. Please refer to the relevant board manuals for information on key connections and supplies.

UM2018 - Rev 3 page 28/35



12 General safety instructions

Danger:

The evaluation board works with high voltage which could be deadly for the users. Furthermore all circuits on the board are not isolated from the line input. Due to the high power density, the components on the board as well as the heat sink can be heated to a very high temperature, which can cause a burning risk when touched directly. This board is intended for use by experienced power electronics professionals who understand the precautions that must be taken to ensure that no danger or risk may occur while operating this board.

Caution:

After the operation of the evaluation board, the bulk capacitor C1 (if used) may still store a high energy for several minutes. So it must be first discharged before any direct touching of the board.

Important:

To protect the bulk capacitor C1, we strongly recommended using an external brake chopper after C1 (to discharge the high brake current back from the induction motor).

UM2018 - Rev 3 page 29/35



13 References

All of the following reference material is freely available on www.st.com

- 1. STGIB10CH60TS-L datasheet
- 2. TSV994 datasheet
- 3. STTH15R06 datasheet
- 4. User manual UM1052 STM32F PMSM single/dual FOC SDK v4.3
- Application note AN4076 Two or three shunt resistor based current sensing circuit design in 3-phase inverters

UM2018 - Rev 3 page 30/35



Revision history

Table 10. Document revision history

Date	Version	Changes
09-Feb-2016	1	Initial release.
		Updated cover page title.
16-Apr-2018	2	Updated key features
10-Αρι-2016		Updated STEVAL-IPM10B circuit schematic (5 of 6)
		Updated bill of material
18-Sep-2019	3	Updated Section 2.1 Schematic diagram

UM2018 - Rev 3 page 31/35



Contents

1	Key	Key features2						
2	Circ	uit sch	ematics	3				
	2.1	Scher	matic diagram	3				
3	Main characteristics							
4	Filte	rs and	key parameters	10				
	4.1	Input	signals	10				
	4.2	Boots	strap capacitor	10				
	4.3	Overd	current protection	10				
		4.3.1	SD Pin	11				
		4.3.2	Fault management					
		4.3.3	Shunt resistor selection	13				
		4.3.4	RC filter	14				
		4.3.5	Single- or three-shunt selection	14				
5	Cur	ent sei	nsing amplifying network	16				
6	Tem	peratui	re monitoring	18				
	6.1	Therm	nal sensor (VTSO)	18				
	6.2	NTC 7	Thermistor	18				
7	Firm	ware c	configuration for STM32 PMSM FOC SDK	20				
8	Con	nectors	s, jumpers and test pins	21				
9	Bill	of mate	erial	24				
10	PCE	desigi	n guide	26				
	10.1	Layou	ut of reference board	26				
11	Rec	ommen	ndations and suggestions	28				
12								
13	References							
Rev			V					



List of tables

Table 1.	Fault timing	11
Table 2.	Shunt selection	14
Table 3.	Op-amp sensing configuration	16
Table 4.	Amplifying networks	17
Table 5.	ST motor control workbench GUI parameters	20
Table 6.	Connectors	21
Table 7.	Jumpers	22
Table 8.	Test pins	22
Table 9.	Bill of materials	24
Table 10.	Document revision history	31



List of figures

Figure 1.	SLLIMM 2nd series motor control internal demo board (top view)	. 1
Figure 2.	SLLIMM 2nd series motor control internal demo board: (bottom view)	. 2
Figure 3.	STEVAL-IPM10B circuit schematic (1 of 6)	. 3
Figure 4.	STEVAL-IPM10B circuit schematic (2 of 6)	. 4
Figure 5.	STEVAL-IPM10B circuit schematic (3 of 6)	. 5
Figure 6.	STEVAL-IPM10B circuit schematic (4 of 6)	. 6
Figure 7.	STEVAL-IPM10B circuit schematic (5 of 6)	. 7
Figure 8.	STEVAL-IPM10B circuit schematic (6 of 6)	. 8
Figure 9.	STEVAL-IPM05F architecture	. 9
Figure 10.	C _{BOOT} graph selection	10
Figure 11.	SD failure due to overcurrent	12
Figure 12.	SD failure due to undervoltage (UVLO below 70 µs)	13
Figure 13.	SD failure due to undervoltage (UVLO above 70 µs)	13
Figure 14.	One-shunt configuration	15
Figure 15.	Three-shunt configuration	15
Figure 16.	Thermal sensor voltage vs temperature	18
Figure 17.	NTC voltage vs temperature	19
Figure 18.	Silk screen and etch - top side	26
Figure 19.	Silk screen and etch - bottom side	27

UM2018 - Rev 3 page 34/35



IMPORTANT NOTICE - PLEASE READ CAREFULLY

STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST's terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers' products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. For additional information about ST trademarks, please refer to www.st.com/trademarks. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2019 STMicroelectronics - All rights reserved

UM2018 - Rev 3 page 35/35